



THE UNITED STATES PATENT AND TRADEMARK OFFICE

#19/B
10/17/2
Suresh

Applicant: Takeshi Nogami
Serial No.: 09/ 915,145
Filed: July 25, 2001
Invention: "SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF"

Atty. Docket No. 075834.00096
Group Art Unit: 2811
Examiner: Thomas J. Magee

AMENDMENT A

Assistant Commissioner of Patents
Washington, D.C. 20231

S I R:

In response to the Office Action dated July 3, 2002, please amend the application as follows:

IN THE CLAIMS:

1. (Once Amended) A semiconductor device comprising:
a conductive member;
a cobalt including layer having oxidation resistive and fluorinated acid resistive
properties formed over said conductive member; and
a clad layer formed over the cobalt including layer for cladding said cobalt including layer.
2. (Once Amended) The semiconductor device as cited in Claim 1, wherein said cobalt including layer [comprising of the] is comprised of a cobalt tungsten phosphor layer.
3. (Once Amended) The semiconductor device as cited in Claim 1, wherein said clad layer [comprising of] is comprised of a cobalt silicide layer.

RECEIVED
OCT 11 2002
TECHNOLOGY CENTER 2800